





TEXAS INSTRUMENTS

SN54AHCT132, SN74AHCT132 SCLS366I – MAY 1997 – REVISED OCTOBER 2023

SN54AHCT132, SN74AHCT132 Quadruple Positive-NAND Gates With Schmitt-trigger Inputs

1 Features

- Operating range of 4.5 V to 5.5 V
- Low power consumption, 10- μ A maximum I_{CC}
- ±8-mA output drive at 5 V
- Operation from very slow input transitions
- Temperature-compensated threshold levels
- High noise immunity
- Same pinouts as 'AHCT00
- Latch-up performance exceeds 250 mA per JESD 17

2 Applications

- Enable or disable a digital signal
- Controlling an indicator LED
- Translation between communication modules and system controllers

3 Description

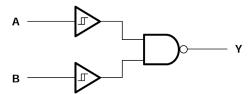
The 'AHCT132 devices are quadruple positive-NAND gates. These devices perform the Boolean function Y = $\overline{A \cdot B}$ or Y = $\overline{A} + \overline{B}$ in positive logic.

Each circuit functions as a NAND gate, but because of the Schmitt action, it has different input threshold levels for positive- and negative-going signals. These circuits are temperature compensated and can be triggered from the slowest of input ramps and still give clean jitter-free output signals.

PART NUMBER	PACKAGE	PACKAGE SIZE	BODY SIZE (NOM)
	D (SOIC, 14)	8.7 mm × 6 mm	8.7 mm × 3.9 mm
	DB (SSOP, 14)	6.2 mm × 7.8 mm	6.2 mm × 5.3 mm
	DGV (TVSOP, 14)	3.6 mm × 6.4 mm	3.6 mm × 4.4 mm
SN74AHCT1 32	N (PDIP, 14)	19.3 mm × 8 mm	19.3 mm × 6.3 mm
	NS (SOP, 14)	10.3 mm × 7.8 mm	10.3 mm × 5.3 mm
	PW (TSSOP, 14)	5 mm × 6.4 mm	5 mm × 4.4 mm
	BQA (WQFN, 14)	3 mm × 2.5 mm	3 mm × 2.5 mm
	J (CDIP, 14)	21.3 mm × 7.6 mm	19.56 mm × 6 mm
SN54AHCT1 32	W (CFP, 14)	9.9 mm × 6.3 mm	9.2 mm × 6.3 mm
	FK (LCCC, 20)	ACKAGE SIZE (NOM) OIC, 14) 8.7 mm × 6 mm 8.7 mm × 3.9 mm SSOP, 14) 6.2 mm × 7.8 mm 6.2 mm × 5.3 mm Y (TVSOP, 3.6 mm × 6.4 mm 3.6 mm × 4.4 mm DIP, 14) 19.3 mm × 8 mm 19.3 mm × 6 mm SOP, 14) 10.3 mm × 7.8 mm 10.3 mm × 6.4 mm SOP, 14) 10.3 mm × 7.8 mm 10.3 mm × 5 mm (TSSOP, 5 mm × 6.4 mm 5 mm × 4.4 m (WQFN, 3 mm × 2.5 mm 3 mm × 2.5 m DIP, 14) 21.3 mm × 7.6 mm 19.56 mm × 10.3 mm SFP, 14) 9.9 mm × 6.3 mm 9.2 mm × 6.3 mm	8.9 mm × 8.9 mm

Package Information⁽¹⁾

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Logic Diagram, Each Gate (Positive Logic)



Table of Contents

1 Features1	
2 Applications1	
3 Description1	
4 Revision History2	
5 Pin Configuration and Functions	
6 Specifications	
6.1 Absolute Maximum Ratings5	
6.2 ESD Ratings5	
6.3 Recommended Operating Conditions5	
6.4 Thermal Information5	
6.5 Electrical Characteristics6	
6.6 Switching Characteristics6	
6.7 Noise Characteristics6	
6.8 Operating Characteristics7	
6.9 Typical Characteristics7	
7 Parameter Measurement Information	
8 Detailed Description9	

8.1 Overview	9
8.2 Functional Block Diagram	9
8.3 Feature Description.	
8.4 Device Functional Modes	
9 Application and Implementation	11
9.1 Application Information	
9.2 Typical Application	
9.3 Power Supply Recommendations	
9.4 Layout	14
10 Device and Documentation Support	
10.1 Receiving Notification of Documentation Updates	
10.2 Support Resources	15
10.3 Trademarks	15
10.4 Electrostatic Discharge Caution	
10.5 Glossary	
11 Mechanical, Packaging, and Orderable	
Information	15

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

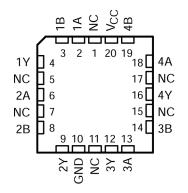
Changes from Revision H (May 2023) to Revision I (October 2023)	Page
• Updated RθJA values: D = 86 to 124.5, PW = 113 to 147.7, all values in °C/W	5
Changes from Revision G (May 1997) to Revision H (May 2023)	Page
Updated the numbering format for tables, figures, and cross-references throughout the doc	
Added BQA package information to the data sheet	1



5 Pin Configuration and Functions

1A 14 VCC 13**1**4B 1B 🛛 2 12 4A 1Y [3 2A 11 **4**Y 4 10 🛛 3B 2B 5 2Y [9 🛛 3A 6 GND [7 8 🛛 3 Y

Figure 5-1. SN54AHCT132 J or W Package SN74AHCT132 D, DB, DGV, N, NS, or PW Package (Top View)



NC – No internal connection



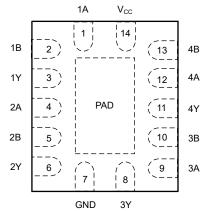


Figure 5-3. SN74AHCT132 BQA Package (Top View)

		PIN				
	SN74AHC		SN54A	HCT132	TYPE ⁽¹⁾	DESCRIPTION
NAME	D, DB, DGV, N, NS, PW	BQA	J, W	FK		
1A	1	1	1	2	I	1A Input
1B	2	2	2	3	0	1Y Output
1Y	3	3	3	4	I	2A Input
2A	4	4	4	6	0	2Y Output
2B	5	5	5	8	I	3A Input
2Y	6	6	6	9	0	3Y Output
3A	9	9	9	13	I	4A Input
3B	10	8	8	14	0	4Y Output
3Y	8	11	11	12	I	5A Input
4A	12	10	10	18	I	5Y Output
4B	13	13	13	19	I	6A Input
4Y	11	12	12	16	0	6Y Output
GND	7	7	7	_		Ground Pin
NC	_	_	_	1, 5, 7, 11, 15, 17	—	No Connection

Table 5-1. Pin Functions

Copyright © 2023 Texas Instruments Incorporated

SN54AHCT132, SN74AHCT132 SCLS366I – MAY 1997 – REVISED OCTOBER 2023



			Table	5-1. FIII FU		lueu)
		PIN				
	SN74AHC	CT132	SN54A	HCT132	TYPE ⁽¹⁾	DESCRIPTION
NAME	D, DB, DGV, N, NS, PW	BQA	J, W	FK		
V _{CC}	14	14	14	20	—	Power Pin

Table 5-1. Pin Functions (continued)

(1) Signal Types: I = Input, O = Output, I/O = Input or Output.

Copyright © 2023 Texas Instruments Incorporated



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
V ₁ ⁽²⁾	Input voltage		-0.5	7	V
V ₀ ⁽²⁾	Output voltage		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	(V ₁ < 0)		-20	mA
I _{OK}	Output clamp current	$(V_O < 0 \text{ or } V_O > V_{CC})$		±20	mA
Io	Continuous output current	$(V_{O} = 0 \text{ to } V_{CC})$		±25	mA
	Continuous current through V_{CC} o	r GND		±50	mA
T _{stg}	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
V (ESD)	Electrostatic discharge	Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1000	v

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		SN54Ał	ICT132	SN74AHC	UNIT	
		MIN	MAX	MIN	MAX	UNIT
V _{CC}	Supply voltage	4.5	5.5	4.5	5.5	V
VI	Input voltage	0	5.5	0	5.5	V
Vo	Output voltage	0	V _{CC}	0	V _{CC}	V
I _{OH}	High-level output current		-8		-8	mA
I _{OL}	Low-level output current		8		8	mA
T _A	Operating free-air temperature	-55	125	-40	85	°C

 All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

6.4 Thermal Information

				S	Nx4AHCT13	2			
		D	DB	DGV	N	NS	PW	BQA	UNIT
THERMAL METRIC ¹		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	124.5	96	127	80	76	147.7	88.3	°C/W

6.5 Electrical Characteristics

DADAMETED	TEST CONDITIONS	V	T _A = 2	25 °C		SN54AH	ICT132	SN74AHCT132		
PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
V _{T+} Positive-		4.5 V	0.9		1.9	0.9	1.9	0.9	1.9	
going input threshold voltage		5.5 V	1		2.1	1	2.1	1	2.1	V
V _{T-} Negative-		4.5 V	0.5		1.5	0.5	1.5	0.5	1.5	
going input threshold voltage		5.5 V	0.6		1.7	0.6	1.7	0.6	1.7	V
ΔV _T Hysteresis		4.5 V	0.3		1.4	0.3	1.4	0.3	1.4	V
(V _{T+} - V _{T-})		5.5 V	0.3		1.5	0.3	1.5	0.3	1.5	v
V _{OH}	I _{OH} = -50 μA	4.5 V	4.4	4.5		4.4		4.4		V
V OH	I _{OH} = -8 mA	4.5 V	3.94			3.8		3.8		v
V	I _{OL} = 50 μA	4.5 V	·		0.1		0.1		0.1	V
V _{OL}	I _{OL} = 8 mA	- 4.5 V	·		0.36		0.5		0.44	v
I _I	V ₁ = 5.5 V or GND	0 V to 5.5 V			±0.1		±1 ⁽¹⁾		±1	μA
I _{CC}	$V_1 = VCC \text{ or GND}, I_0 = 0$	5.5 V			2		20		20	μA
ΔI _{CC} ⁽²⁾	One input at 3.4 V, Other inputs at V_{CC} or GND	5.5 V			1.35		1.5		1.5	mA
Ci	V _I = V _{CC} or GND	5 V		2	10				10	pF

over recommended operating free-air temperature range (unless otherwise noted)

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested at V_{CC} = 0 V.

(2) This is the increase in supply current for each input at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

6.6 Switching Characteristics

over recommended operating free-air temperature range, $V_{CC} = 5 V \pm 0.5 V$ (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM	то	LOAD	T⊿	(= 25°C	;	SN54AH0	CT132	SN74AH	CT132	UNIT	
(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT		
t _{PLH}	A or P	V	C _L = 15 pF		5.5 <mark>(1)</mark>	8 ⁽¹⁾	1 ⁽¹⁾	ς 9 <mark>(1)</mark>	1	9	ns	
t _{PHL}	A or B	AUB	I	CL = 15 pr		4.5 <mark>(1)</mark>	6 <mark>(1)</mark>	1 ⁽¹⁾	7 ⁽¹⁾	1	7	115
t _{PLH}	A or B	v	С _L = 50 рF		6.5	9	1	10	1	10	ns	
t _{PHL}		I	0 <u> </u>		5.5	7	1	8	1	8	115	

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested.

6.7 Noise Characteristics

 $V_{CC} = 5 V, C_L = 50 pF, T_A = 25^{\circ}C^{(1)}$

	PARAMETER	SN74AF	SN74AHCT132					
	PARAMETER	MIN	TYP	MAX	UNIT			
V _{OL(P)}	Quiet output, maximum dynamic V _{OL}		0.5	0.8	V			
V _{OL(V)}	Quiet output, minimum dynamic V _{OL}		-0.28	-0.8	V			
V _{OH(V)}	Quiet output, minimum dynamic V _{OH}		5		V			
V _{IH(D)}	High-level dynamic input voltage	2			V			
V _{IL(D)}	Low-level dynamic input voltage			0.8	V			

(1) Characteristics are for surface-mount packages only.



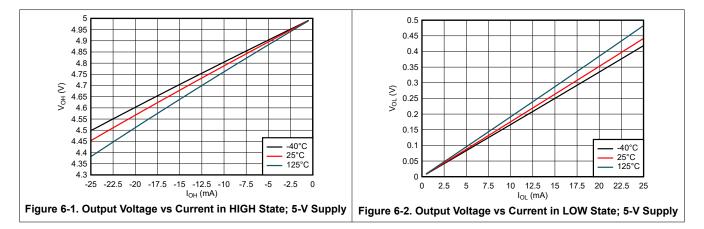
6.8 Operating Characteristics

V_{CC} = 5 V, T_A = 25°C

	PARAMETER	TEST CO	NDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance	No load,	f = 1 MHz	15	pF

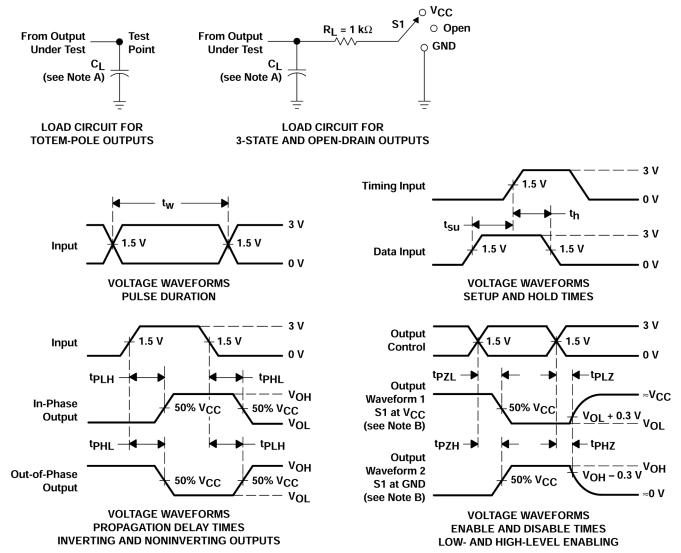
6.9 Typical Characteristics

T_A = 25°C (unless otherwise noted)





7 Parameter Measurement Information



- A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_r \leq 3 ns, t_f \leq 3 ns.
- D. The outputs are measured one at a time with one input transition per measurement.

Figure 7-1.	Load Circ	uit and Vol	tage Waveforms	5

TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{CC}
t _{PHZ} /t _{PZH}	GND
Open Drain	V _{CC}



8 Detailed Description

8.1 Overview

The 'AHCT132 devices are quadruple positive-NAND gates.

These devices perform the Boolean function $Y = \overline{A \cdot B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

Each circuit functions as a NAND gate, but because of the Schmitt action, it has different input threshold levels for positive- and negative-going signals.

These circuits are temperature compensated and can be triggered from the slowest of input ramps and still give clean jitter-free output signals.

8.2 Functional Block Diagram

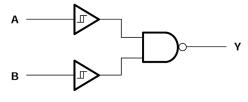


Figure 8-1.

8.3 Feature Description

8.3.1 TTL-Compatible Schmitt-Trigger CMOS Inputs

This device includes TTL-compatible CMOS inputs with Schmitt-trigger architecture. These inputs are specifically designed to interface with TTL logic devices by having a reduced input voltage thresholds.

TTL-compatible Schmitt-trigger CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see Understanding Schmitt Triggers.

Do not leave TTL-compatible CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors, however a 10-k Ω resistor is recommended and will typically meet all requirements.

8.3.2 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.



8.3.3 Clamp Diode Structure

As Figure 8-2 shows, the outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only.

CAUTION Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

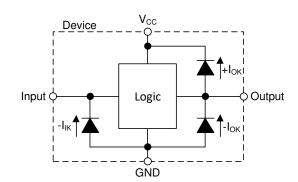


Figure 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

Table 8-1. Function Table (Each Gate)							
IN	PUTS	Ουτρυτ γ					
Α	В	0019011					
Н	Н	L					
L	Х	н					
Х	L	Н					



9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

In this application, two 2-input NAND gates are used to create an active-low SR latch as shown in *Typical Application*. The two additional gates can be used for a second SR latch, or the inputs can be grounded and both channels left unused.

The AHCT132 is used to drive the tamper indicator LED and provide one bit of data to the system controller. When the tamper switch outputs LOW, the output Q becomes HIGH. This output remains HIGH until the system controller addresses the event and sends a LOW signal to the \overline{R} input which returns the Q output back to LOW.

The inputs of this active-low SR latch can often be driven by open-drain outputs which can produce slow input transition rates when they transition from LOW to Hi-Z. This makes the AHCT132 ideal for the application because it has Schmitt-trigger inputs that do not have input transition rate requirements.

9.2 Typical Application

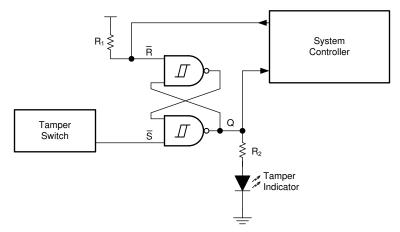


Figure 9-1. Typical Application Block Diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SNx4AHCT132 plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SNx4AHCT132 plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground

Copyright © 2023 Texas Instruments Incorporated



connection. Be sure to not exceed the maximum total current through GND listed in the Absolute Maximum Ratings.

The SNx4AHCT132 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.



The SNx4AHCT132 can drive a load with total resistance described by $R_L \ge V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.

Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear* and Logic (SLL) Packages and Devices.

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{t-(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SNx4AHCT132 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k Ω resistor value is often used due to these factors.

The SNx4AHCT132 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the Feature Description section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.

Copyright © 2023 Texas Instruments Incorporated



- Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; by design, however, it will
 optimize performance. This can be accomplished by providing short, appropriately sized traces from the
 SNx4AHCT132 to one or more of the receiving devices.
- Ensure the resistive load at the output is larger than (V_{CC} / I_{O(max)}) Ω. Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in MΩ; much larger than the minimum calculated previously.
- 4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

9.2.3 Application Curves

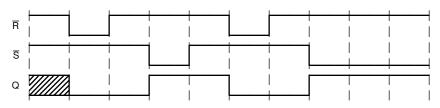


Figure 9-2. Application Timing Diagram

9.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

9.4 Layout

9.4.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

9.4.2 Layout Example

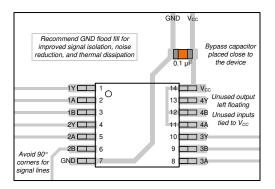


Figure 9-3. Example layout for the SN74AHCT132



10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

10.3 Trademarks

TI E2E[™] is a trademark of Texas Instruments. All trademarks are the property of their respective owners.

10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	(.)					(=)	(6)	(0)		()	
SN74AHCT132BQAR	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	AHT132	Samples
SN74AHCT132D	OBSOLETE	SOIC	D	14		TBD	Call TI	Call TI	-40 to 85	AHCT132	
SN74AHCT132DBR	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HB132	Samples
SN74AHCT132DGVR	ACTIVE	TVSOP	DGV	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HB132	Samples
SN74AHCT132DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	AHCT132	Samples
SN74AHCT132N	ACTIVE	PDIP	Ν	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74AHCT132N	Samples
SN74AHCT132NSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	AHCT132	Samples
SN74AHCT132PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	HB132	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

www.ti.com

Texas

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal	2				0					r.		t.
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHCT132BQAR	WQFN	BQA	14	3000	180.0	12.4	2.8	3.3	1.1	4.0	12.0	Q1
SN74AHCT132DBR	SSOP	DB	14	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN74AHCT132DGVR	TVSOP	DGV	14	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74AHCT132DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74AHCT132DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74AHCT132DR	SOIC	D	14	2500	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1
SN74AHCT132NSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN74AHCT132PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74AHCT132PWR	TSSOP	PW	14	2000	330.0	12.4	6.85	5.45	1.6	8.0	12.0	Q1
SN74AHCT132PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



www.ti.com

PACKAGE MATERIALS INFORMATION

14-Jun-2024



Device Package Type		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AHCT132BQAR	WQFN	BQA	14	3000	210.0	185.0	35.0
SN74AHCT132DBR	SSOP	DB	14	2000	356.0	356.0	35.0
SN74AHCT132DGVR	TVSOP	DGV	14	2000	356.0	356.0	35.0
SN74AHCT132DR	SOIC	D	14	2500	353.0	353.0	32.0
SN74AHCT132DR	SOIC	D	14	2500	356.0	356.0	35.0
SN74AHCT132DR	SOIC	D	14	2500	340.5	336.1	32.0
SN74AHCT132NSR	SO	NS	14	2000	356.0	356.0	35.0
SN74AHCT132PWR	TSSOP	PW	14	2000	356.0	356.0	35.0
SN74AHCT132PWR	TSSOP	PW	14	2000	366.0	364.0	50.0
SN74AHCT132PWR	TSSOP	PW	14	2000	353.0	353.0	32.0

TEXAS INSTRUMENTS

www.ti.com

14-Jun-2024

TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
SN74AHCT132N	N	PDIP	14	25	506	13.97	11230	4.32

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2024, Texas Instruments Incorporated